

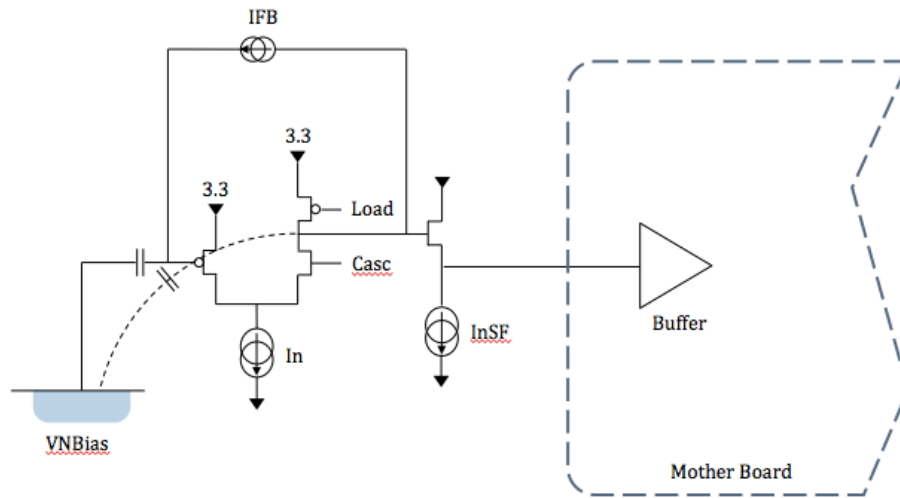


Laser test on CHESI chip

Vitaliy Fadeyev, Zach Galloway , Herve Grabas
Alexander Grillo , Zhijun Liang , Abe Seiden
Jennifer Volk, Forest Martinez-Mckinney

University of California, Santa Cruz

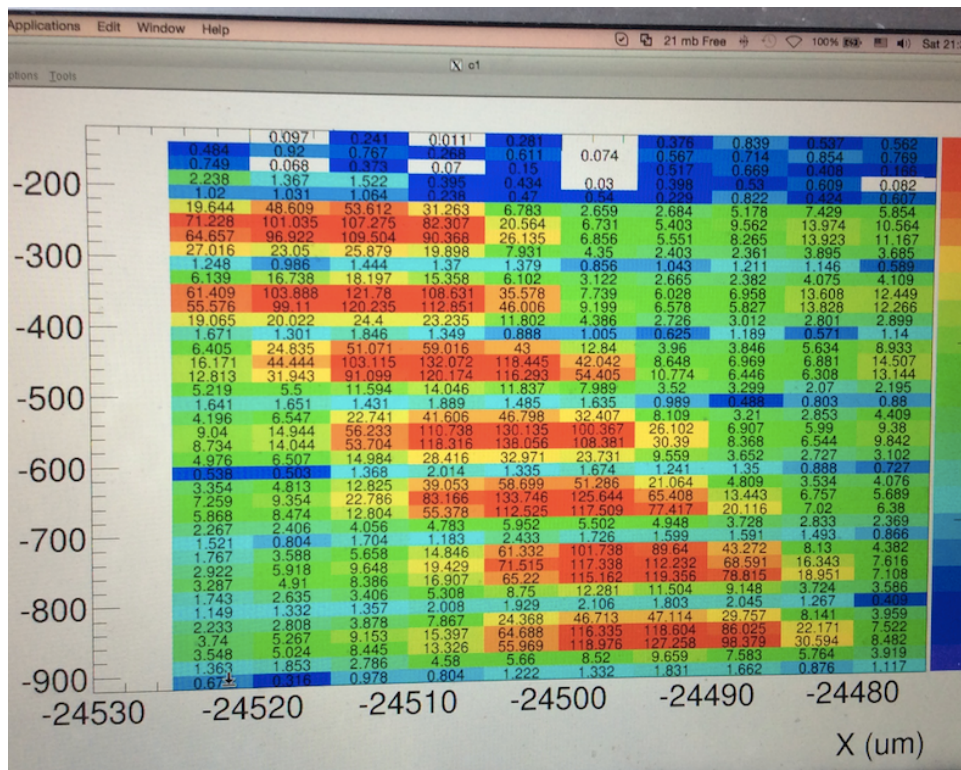
Amplifier biases setup for CHESS I active pixel testing



	Config 7	Config 8
VPFB	2.664V	2.7V
VNSF	0.57	0.75
VCasc	2.6V	2.6V
VPload	2.1V	2.1V
VN	1V	1V
VNBias	340mV	150mV

Laser focusing and 2D scan

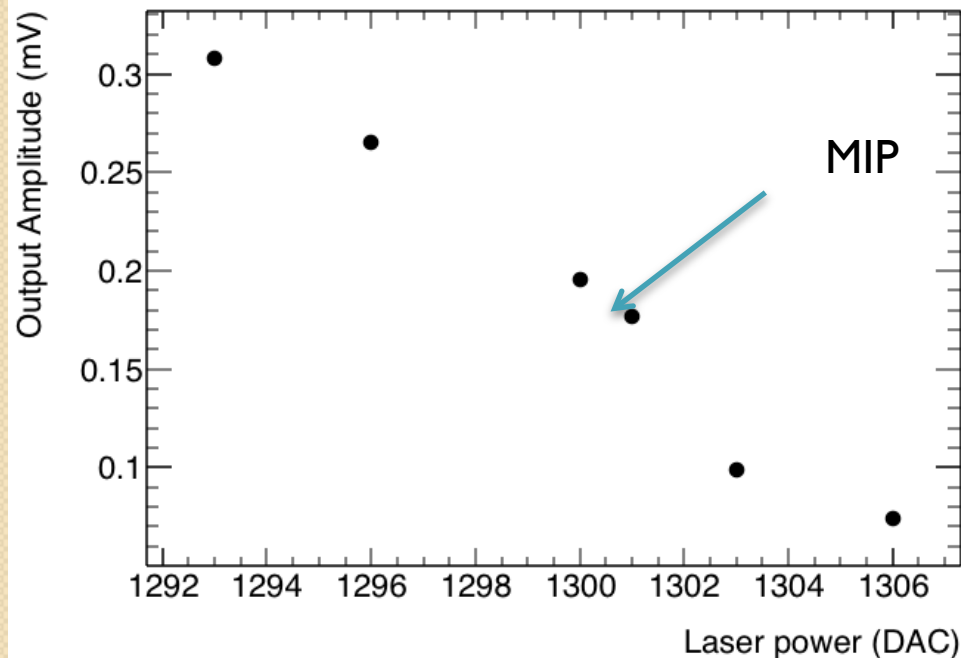
- IR Laser is focused to about 5um beam spot size.
- A 2D scan on one pixel in APA07 (45X800um).
 - N-well can be clearly seen.



Laser power VS output amplitude

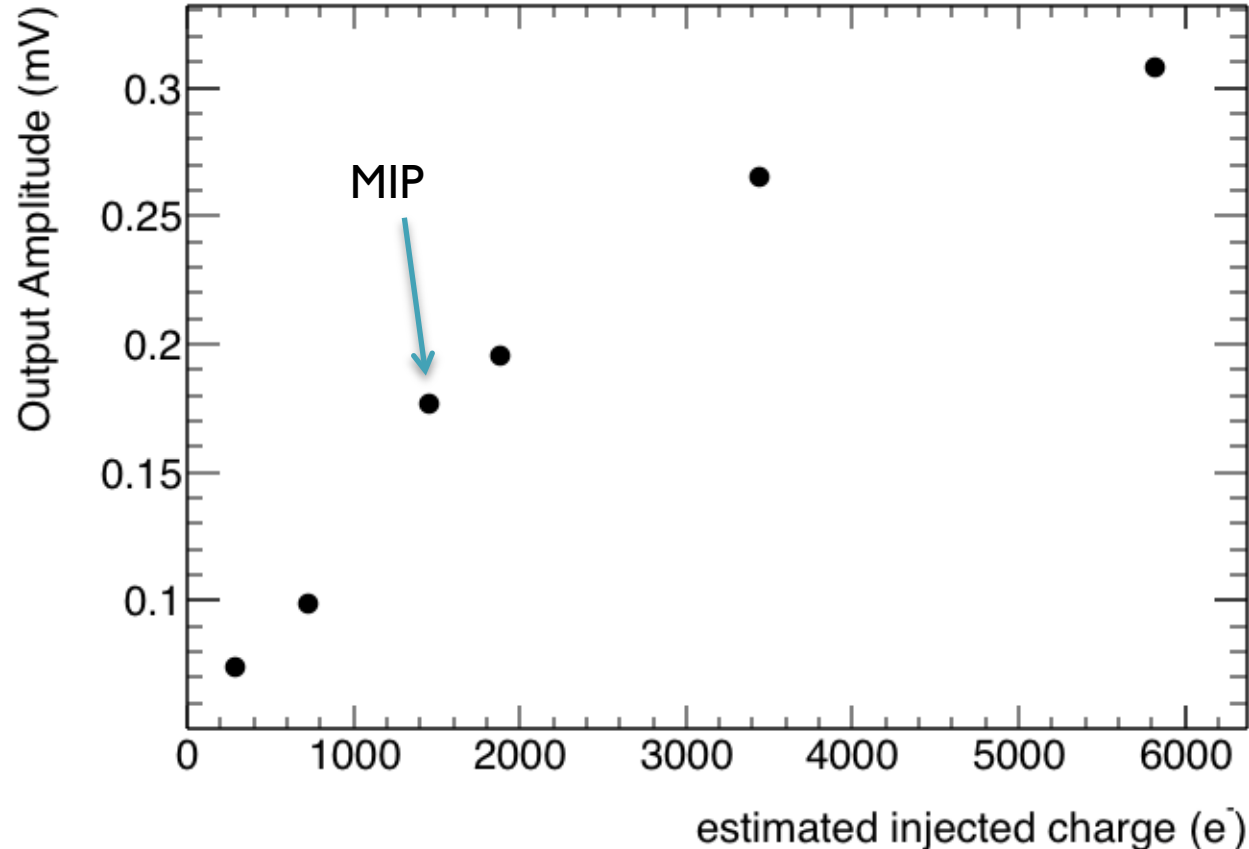
- Try to reproduce the charge deposition of MIP using focused laser beam.
- But it is not very sure which laser power value corresponding to MIP
 - Check CHESS1 signal output in different laser power

$V_{\text{bias}} = 120\text{V}$, config 8



Injected charge VS output amplitude

- Based on the calibration by Zach.
- We correlated the laser power with estimated injected charge.

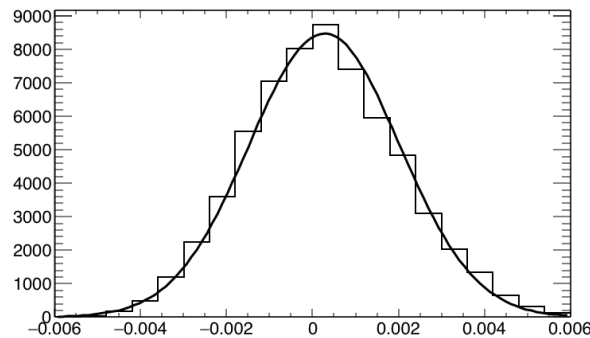
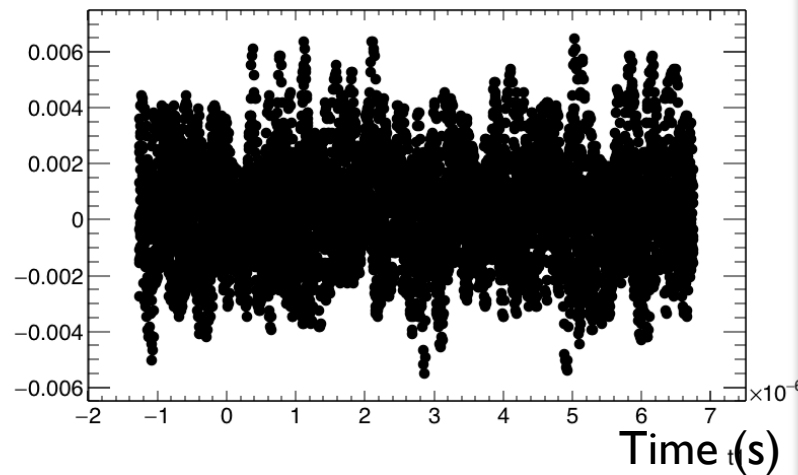


Signal pulse in MIP (config 8)

- Signal to noise study
 - Signal amplitude in charge deposition of MIP is about 180mV
 - Noise level is about 1.8mV
 - Signal to noise ratio is about 100 before irradiation using config 8.

Noise

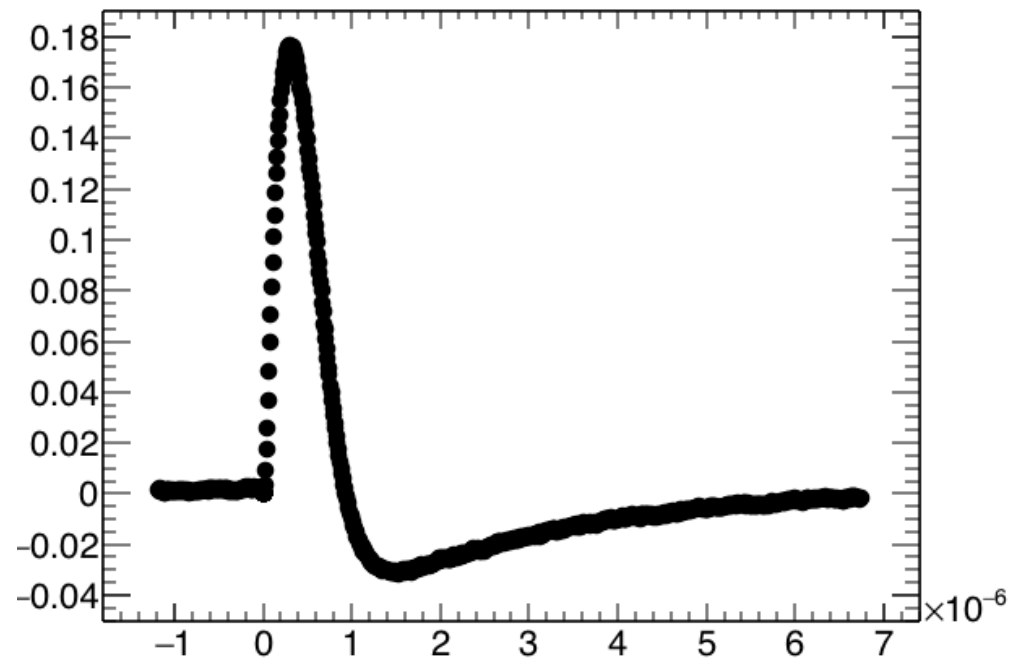
Output amplitude (V)



Output amplitude (V)

MIP Signal (emulated with laser)

$V_{\text{bias}} = 120\text{V}, \text{APA07}$

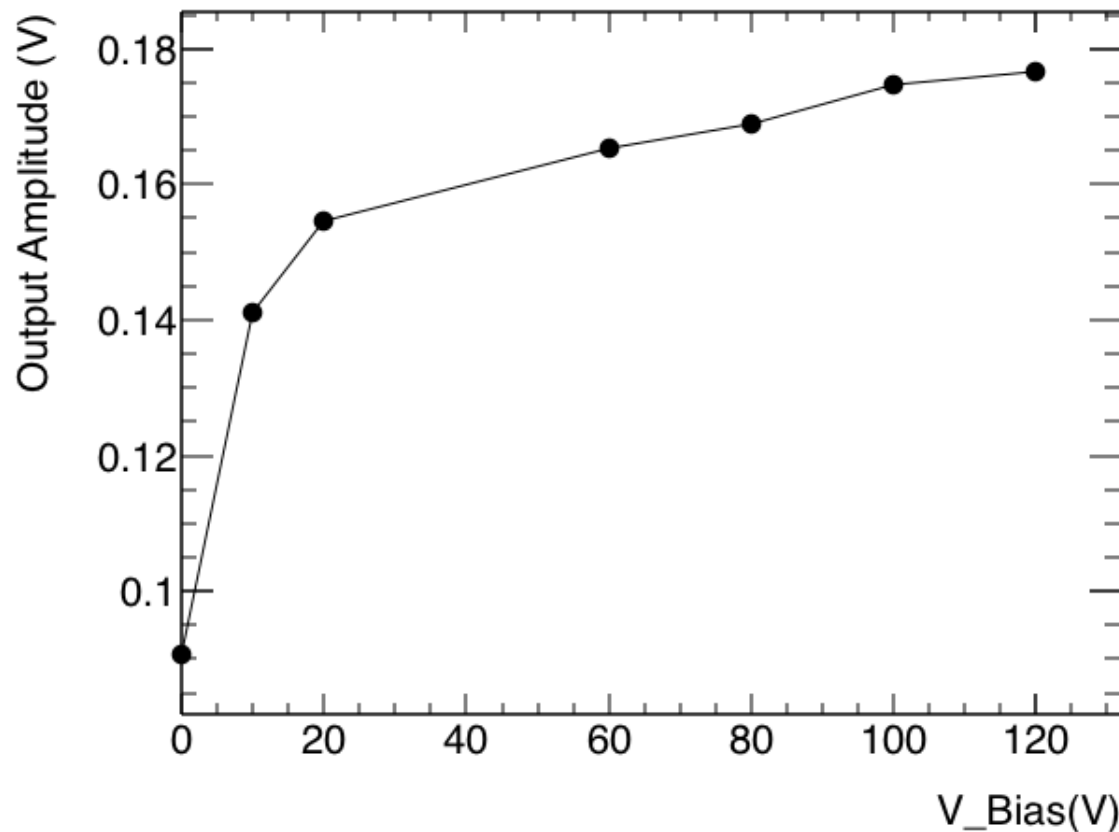


Time (s)

HV bias dependence

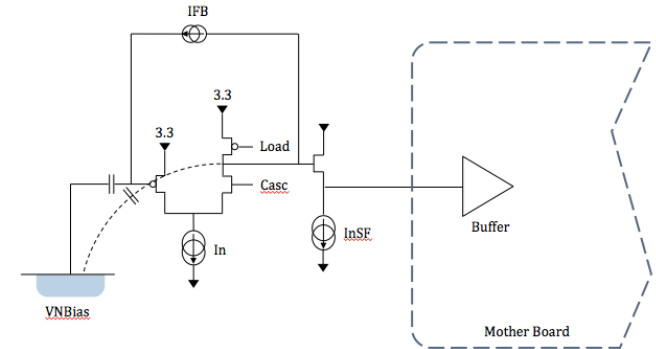
- Output amplitude is about 90mV without HV bias.
- After HV bias, output amplitude is 180mV
- Saturated at 20V ?

MIP Signal (emulated with laser), APA07

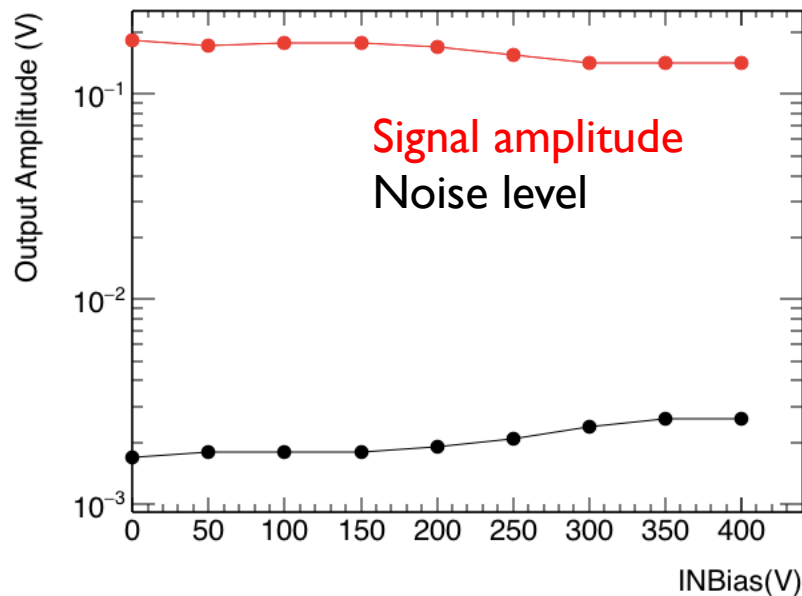


Modifying VNBias

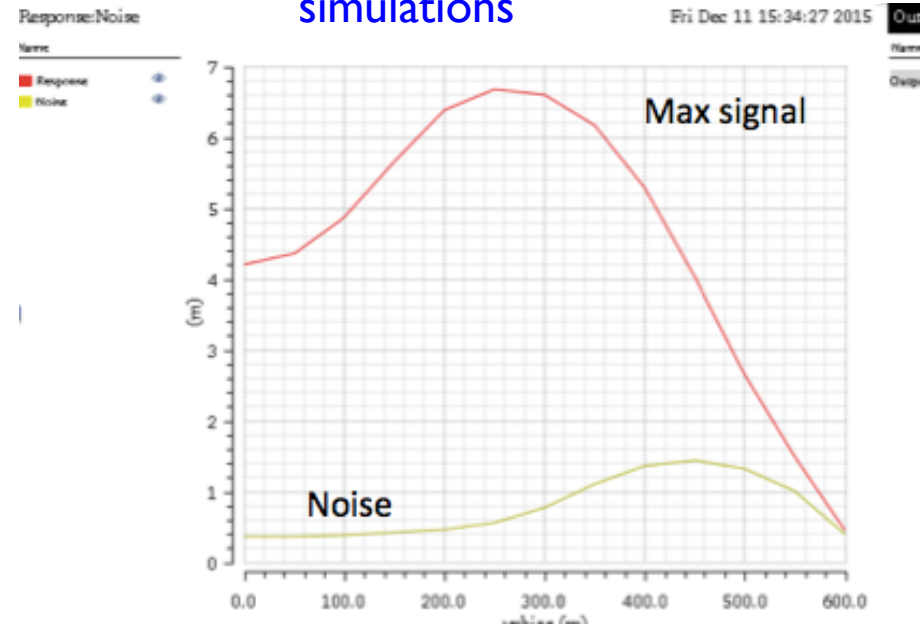
- VNBias controls the bias of the Pixel diode. Value shouldn't be changed .
- Simulations and measurements are quite different for VNBias dependence.



measurements



simulations



Summary

- Use laser to emulate the charge deposition of MIP.
- Study signal to noise ratio of active pixel in CHESS I.
 - Signal amplitude is about 180mV
 - Noise level is about 1.8mV
 - Signal to noise ratio is about 100.
- V_{bias} dependence is also studied
 - Saturated at 20V